L Number	Hits	Search Text	DB	Time stamp
-	149	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad$5 near layer) and indium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:41
-	131	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad$5 near layer) and indium and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:50
-	20	(nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad$5 near layer) and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:22
-	28	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad$5 near layer) and indium and substrate and electrode and absorb$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	21	((nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad$5 near layer) and indium and substrate and electrode and absorb$6) not ((nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad$5 near layer) and substrate and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	6	(laser near chip) and (photoelectric or (photo adj electric)) and block$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:42
-	160	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:44
-	14	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:46
-	171	(laser near semiconductor) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo ajd diode)) and block$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:00
-	72	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo ajd diode)) and block$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:03
-	40	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) and block$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 10:59
-	23	((semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) and block$6 and buffer and substrate) and 372/$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:29

-	5	(semiconductor near laser near3 chip) and ((photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) same block$6) and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 10:58
-	0	(semiconductor near laser near3 chip) and ((photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) same (block$6 near layer)) and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 11:01
-	26	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) or (photodiode) or (photo adj detector) or (photo adj diode)) and (block$6 near layer) and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 11:02